



MMST3906

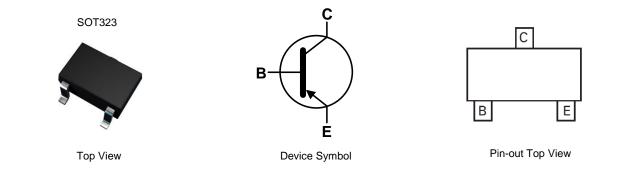
40V PNP SMALL SIGNAL TRANSISTOR IN SOT323

Features

- BV_{CEO} > -40V
- I_C = -200mA Collector Current
- Epitaxial Planar Die Construction
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMST3904
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



Ordering Information (Note 4)

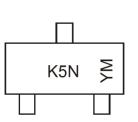
Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel	
MMST3906-7-F	Active	AEC-Q101	K5N	7	8	3,000	
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.							

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K5N = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M or \overline{M} = Month (ex: 9 = September)

Date	Code	Key
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2410 0040													
Year	201	5	2016	2017	2018	2019	2020	202	1 20	22	2023	2024	2025
Code	С		D	E	F	G	Н	I		J	К	L	М
Mont	h	Ja	an Fe	b Ma	r Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	;	1		2 3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current	Ic	-200	mA

Thermal Characteristics (@TA = +25°C unless otherwise specified.)

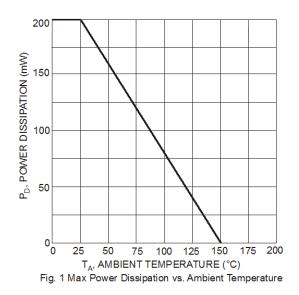
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	Pd	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	625	°C/W
Operating and Storage Temperature Range	T _i , T _{STG}	-55 to +150	°C

ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is Notes: measured under still air conditions whilst operating in a steady-state. 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information





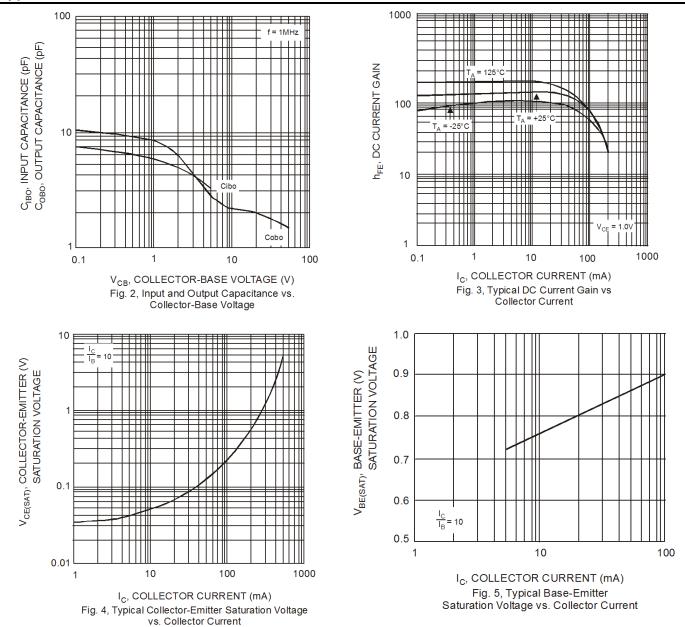
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

				T	
	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	DV/	40		V	40.44
Collector-Base Breakdown Voltage	BV _{CBO}	-40	—	V	$I_{C} = -10\mu A, I_{E} = 0$
Collector-Emitter Breakdown Voltage	BV _{CEO}	-40	—		$I_{\rm C} = -1 \rm{mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-5		V	$I_{\rm E} = -10\mu A, I_{\rm C} = 0$
Collector Cutoff Current	ICEX	—	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3V$
Base Cutoff Current	I _{BL}	—	-50	nA	$V_{CE} = -30V, V_{EB(OFF)} = -3V$
ON CHARACTERISTICS (Note 7)			1	1	
		60	—		$I_{C} = -100\mu A, V_{CE} = -1V$
		80	_		$I_C = -1mA$, $V_{CE} = -1V$
DC Current Gain	h _{FE}	100 60	300		$I_{C} = -10 \text{mA}, V_{CE} = -1 \text{V}$
		80 30	_		$I_{C} = -50 \text{mA}, V_{CE} = -1 \text{V}$
		00			$I_{C} = -100 \text{mA}, V_{CE} = -1 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_	-0.20	V	$I_{C} = -10mA$, $I_{B} = -1mA$
-	()		-0.30		$I_{\rm C} = -50 {\rm mA}, I_{\rm B} = -5 {\rm mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}	-0.65	-0.85	V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = -1 {\rm mA}$
SMALL SIGNAL CHARACTERISTICS	22(000)		-0.95		$I_{\rm C} = -50 {\rm mA}, I_{\rm B} = -5 {\rm mA}$
Output Capacitance			4.5	~ [
	Сово		-	pF	$V_{CB} = -5V, f = 1.0MHz, I_E = 0$
Input Capacitance	CIBO		10	pF	$V_{EB} = -0.5V, f = 1.0MHz, I_{C} = 0$
Input Impedance	h _{IE}	2	12	kΩ	-
Voltage Feedback Ratio	h _{RE}	0.1	10	x 10⁻⁴	$V_{CE} = 1V, I_{C} = 10mA,$
Small Signal Current Gain	HFE	100	400	—	f = 1kHz
Output Admittance	h _{OE}	3	60	μS	
Current Gain-Bandwidth Product	f⊤	300	—	MHz	$V_{CE} = -20V, I_C = -10mA, f = 100MHz$
Noise Figure	NF	_	4	dB	$V_{CE} = -5V$, $I_C = -100\mu A$, R _S = 1k Ω , f = 1kHz
SWITCHING CHARACTERISTICS	1				- 7
Delay Time	t _d	_	35	ns	$V_{CC} = -3V, I_{C} = -10mA,$
Rise Time	tr		35	ns	$I_{B1} = -1mA, V_{BE(off)} = 0.5V$
Storage Time	ts		225	ns	$V_{CC} = -3V, I_{C} = -10mA,$
Fall Time	t _f		75	ns	$I_{B1} = I_{B2} = -1mA$

Note: 7. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



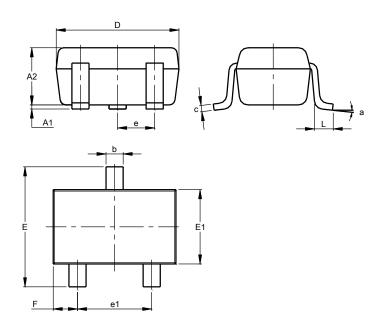
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

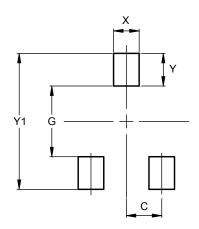
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT323							
Dim	Min	Тур						
A1	0.00	0.10	0.05					
A2	0.90	1.00	0.95					
b	0.25	0.40	0.30					
С	0.10	0.18	0.11					
D	1.80	2.20	2.15					
Е	2.00	2.20	2.10					
E1	1.15	1.35	1.30					
е	C).650 B	SC					
e1	1.20	1.40	1.30					
F	0.375	0.475	0.425					
L	0.25	0.40	0.30					
а	0°	8°						
All	Dimen	sions i	in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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